直流 (DC) 电机驱动器 IC

查询样品：**DRV8802**

特性

- 双通道 **H** 桥电流控制电机驱动器
  - 可驱动两个 **DC** 电机
  - 制动模式
  - **2** 位绕组电流控制支持高达 **4** 个电流级
  - 低 **MOSFET** 导通电阻
- **24 V**、**25°C** 下 **1.6 A** 的最大驱动器电流
- 内置 **3.3 V** 基准输出
- 业界标准的并行数字控制接口
- **8 V** 至 **45 V** 宽泛工作电源电压范围
- 耐热性能增强型表面贴装式封装

应用

- 打印机
- 扫描仪
- 办公自动化设备
- 游戏机
- 工厂自动化
- 机器人

说明

DRV8802 可为打印机、扫描仪以及其它自动化设备应用提供集成型电机驱动器解决方案。 该器件具有一个 H 桥驱动器，可驱动一个 DC 电机。 每个 H 桥的输出驱动器模块由 N 沟道功率 MOSFET 组成，这些 MOSFET 被配置成 H 桥，以驱动电机绕组。 DRV8802 可为每个 H 桥提供高达 1.6 A 的峰值电流或 1.1 A 的 RMS 输出电流（在 24 V 与 25°C 下提供适当的散热）。

一个简单的并行数字控制接口可兼容业界标准器件。 衰减模式是可编程的，以在停用时实现电机的制动或惯性滑行。

内部关断功能支持过流保护、短路保护、欠压锁定以及过温保护。

DRV8802 采用 28 引脚 HTSSOP 封装，具有 PowerPAD™ （环保型：符合 RoHS 标准且不含锑/溴）。

订购信息(1)

T_A	封装(2)		可订购部件号 型号	正面 标记
−40°C 至 85°C	PowerPAD™ (HTSSOP) - PWP	2000 卷带	DRV8802PWPR	8802

(1) 有关最新的封装和订购信息，请参阅本文档结尾的“封装选项附录”，或访问 TI 网站： www.ti.com。
(2) 封装图样、热数据和符号可登录 www.ti.com/packaging 获取。

DEVICE INFORMATION

Functional Block Diagram

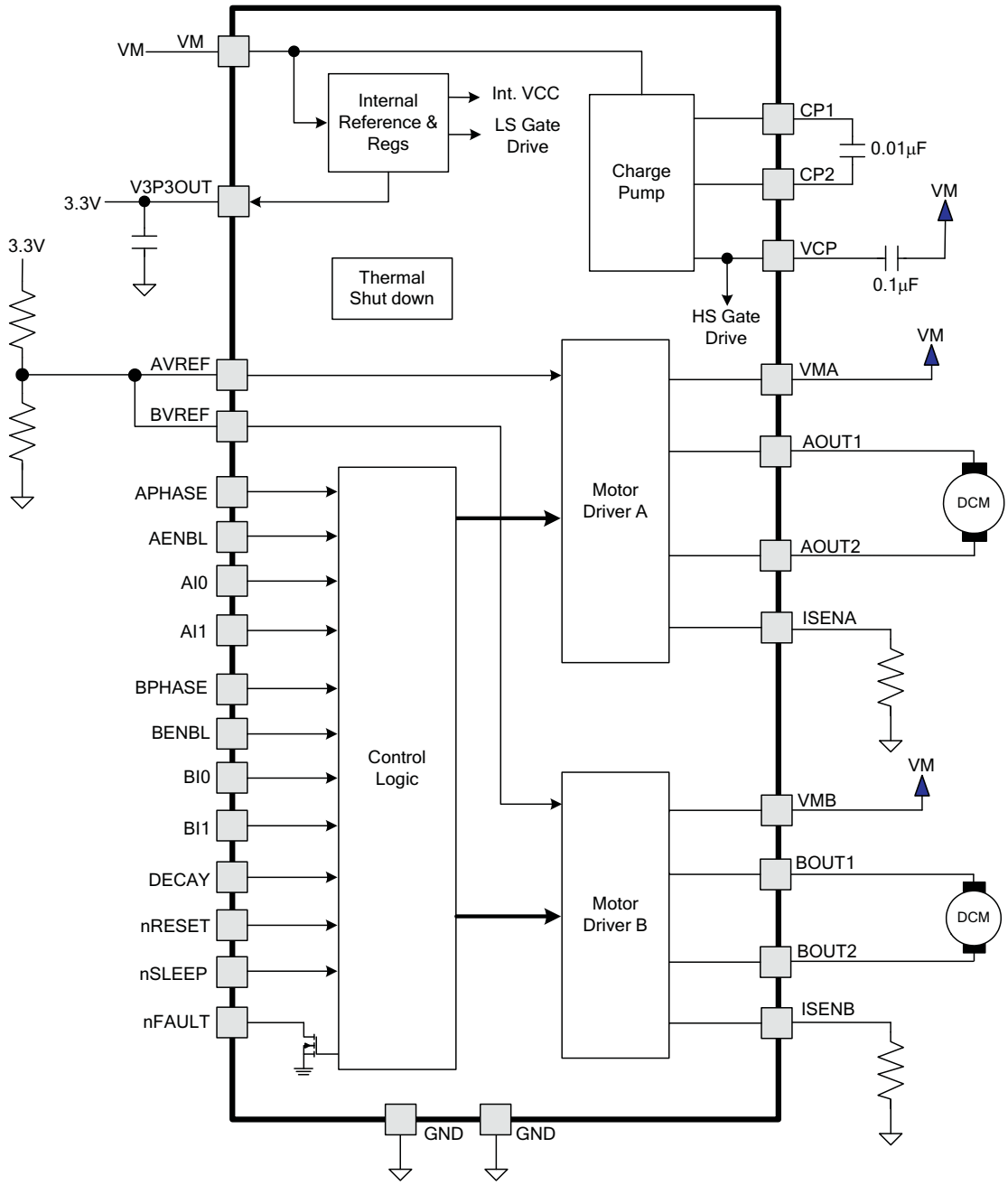
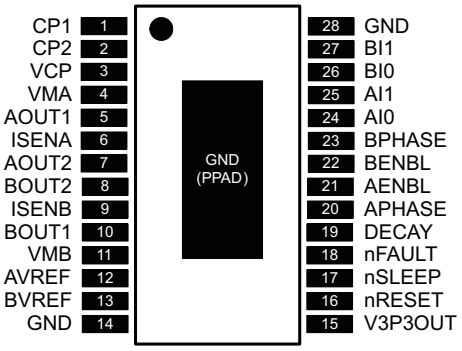


表 1. TERMINAL FUNCTIONS

NAME	PIN	I/O(1)	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS
POWER AND GROUND				
GND	14, 28	-	Device ground	
VMA	4	-	Bridge A power supply	Connect to motor supply (8 - 45 V). Both pins must be connected to same supply.
VMB	11	-	Bridge B power supply	
V3P3OUT	15	O	3.3-V regulator output	Bypass to GND with a 0.47-µF 6.3-V ceramic capacitor. Can be used to supply VREF.
CP1	1	IO	Charge pump flying capacitor	Connect a 0.01-µF 50-V capacitor between CP1 and CP2.
CP2	2	IO	Charge pump flying capacitor	
VCP	3	IO	High-side gate drive voltage	Connect a 0.1-µF 16-V ceramic capacitor to VM.
CONTROL				
AENBL	21	I	Bridge A enable	Logic high to enable bridge A
APHASE	20	I	Bridge A phase (direction)	Logic high sets AOUT1 high, AOUT2 low
AI0	24	I	Bridge A current set	Sets bridge A current: 00 = 100%, 01 = 71%, 10 = 38%, 11 = 0
AI1	25	I		
BENBL	22	I	Bridge B enable	Logic high to enable bridge B
BPHASE	23	I	Bridge B phase (direction)	Logic high sets BOUT1 high, BOUT2 low
BI0	26	I	Bridge B current set	Sets bridge B current: 00 = 100%, 01 = 71%, 10 = 38%, 11 = 0
BI1	27	I		
DECAY	19	I	Decay (brake) mode	Low = brake (slow decay), high = coast (fast decay)
nRESET	16	I	Reset input	Active-low reset input initializes internal logic and disables the H-bridge outputs
nSLEEP	17	I	Sleep mode input	Logic high to enable device, logic low to enter low-power sleep mode
AVREF	12	I	Bridge A current set reference input	Reference voltage for winding current set. Can be driven individually with an external DAC for microstepping, or tied to a reference (e.g., V3P3OUT).
BVREF	13	I	Bridge B current set reference input	
STATUS				
nFAULT	18	OD	Fault	Logic low when in fault condition (overtemp, overcurrent)
OUTPUT				
ISENA	6	IO	Bridge A ground / Isense	Connect to current sense resistor for bridge A
ISENB	9	IO	Bridge B ground / Isense	Connect to current sense resistor for bridge B
AOUT1	5	O	Bridge A output 1	Connect to motor winding A
AOUT2	7	O	Bridge A output 2	
BOUT1	10	O	Bridge B output 1	Connect to motor winding B
BOUT2	8	O	Bridge B output 2	

(1) Directions: I = input, O = output, OZ = tri-state output, OD = open-drain output, IO = input/output

PWP PACKAGE
(TOP VIEW)



ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1) (2)

		VALUE	UNIT
VMx	Power supply voltage range	–0.3 to 47	V
	Digital pin voltage range	–0.5 to 7	V
VREF	Input voltage	–0.3 to 4	V
	ISENSEx pin voltage	–0.3 to 0.8	V
	Peak motor drive output current, t < 1 µS	Internally limited	A
	Continuous motor drive output current(3)	1.6	A
	Continuous total power dissipation	See Dissipation Ratings table	
T_J	Operating virtual junction temperature range	–40 to 150	°C
T_A	Operating ambient temperature range	–40 to 85	°C
T_{stg}	Storage temperature range	–60 to 150	°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal.
(3) Power dissipation and thermal limits must be observed.

DISSIPATION RATINGS (PRELIMINARY)

BOARD	PACKAGE	$R_{\theta JA}$	DERATING FACTOR ABOVE T_A = 25°C	T_A < 25°C	T_A = 70°C	T_A = 85°C
Low-K(1)	PWP	67.5°C/W	14.8 mW/°C	1.85 W	1.18 W	0.96 W
Low-K(2)		39.5°C/W	25.3 mW/°C	3.16 W	2.02 W	1.64 W
High-K(3)		33.5°C/W	29.8 mW/°C	3.73 W	2.38 W	1.94 W
High-K(4)		28°C/W	35.7 mW/°C	4.46 W	2.85 W	2.32 W

(1) The JEDEC Low-K board used to derive this data was a 76-mm x 114-mm, 2-layer, 1.6-mm thick PCB with no backside copper.
(2) The JEDEC Low-K board used to derive this data was a 76-mm x 114-mm, 2-layer, 1.6-mm thick PCB with 25-cm^2 2-oz copper on back side.
(3) The JEDEC High-K board used to derive this data was a 76-mm x 114-mm, 4-layer, 1.6-mm thick PCB with no backside copper and solid 1-oz internal ground plane.
(4) The JEDEC High-K board used to derive this data was a 76-mm x 114-mm, 4-layer, 1.6-mm thick PCB with 25-cm^2 1-oz copper on back side and solid 1-oz internal ground plane.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_M	Motor power supply voltage range(1)	8.2		45	V
V_{REF}	VREF input voltage(2)	1		3.5	V
I_{V3P3}	V3P3OUT load current			1	mA

(1) All V_M pins must be connected to the same supply voltage.
(2) Operational at VREF between 0 V and 1 V, but accuracy is degraded.

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES						
I_{VM}	VM operating supply current	V_M = 24 V, f_{PWM} < 50 kHz		5	8	mA
I_{VMQ}	VM sleep mode supply current	V_M = 24 V		10	20	µA
V_{UVLO}	VM undervoltage lockout voltage	V_M rising		7.8	8.2	V
V3P3OUT REGULATOR						
V_{3P3}	V3P3OUT voltage	IOUT = 0 to 1 mA, V_M = 24 V, T_J = 25°C	3.18	3.30	3.42	V
		IOUT = 0 to 1 mA	3.10	3.30	3.50	
LOGIC-LEVEL INPUTS						
V_{IL}	Input low voltage			0.6	0.7	V
V_{IH}	Input high voltage		2		5.25	V
V_{HYS}	Input hysteresis			0.45		V
I_{IL}	Input low current	VIN = 0	–20		20	µA
I_{IH}	Input high current	VIN = 3.3 V			100	µA
nFAULT OUTPUT (OPEN-DRAIN OUTPUT)						
V_{OL}	Output low voltage	I_O = 5 mA			0.5	V
I_{OH}	Output high leakage current	V_O = 3.3 V			1	µA
DECAY INPUT						
V_{IL}	Input low threshold voltage	For slow decay mode	0		0.8	V
V_{IH}	Input high threshold voltage	For fast decay mode	2			V
I_{IN}	Input current				±40	µA
H-BRIDGE FETS						
$R_{DS(ON)}$	HS FET on resistance	V_M = 24 V, I_O = 1 A, T_J = 25°C		0.63		Ω
		V_M = 24 V, I_O = 1 A, T_J = 85°C		0.76	0.90	
$R_{DS(ON)}$	LS FET on resistance	V_M = 24 V, I_O = 1 A, T_J = 25°C		0.65		Ω
		V_M = 24 V, I_O = 1 A, T_J = 85°C		0.78	0.90	
I_{OFF}	Off-state leakage current		–20		20	µA
MOTOR DRIVER						
f_{PWM}	Internal PWM frequency			50		kHz
t_{BLANK}	Current sense blanking time			3.75		µs
t_R	Rise time	V_M = 24 V	100		360	ns
t_F	Fall time	V_M = 24 V	80		250	ns
t_{DEAD}	Dead time			400		ns
t_{DEG}	Input deglitch time		1.3		2.9	µs
PROTECTION CIRCUITS						
I_{OCP}	Overcurrent protection trip level		1.8		5	A
t_{TSD}	Thermal shutdown temperature	Die temperature	150	160	180	°C

ELECTRICAL CHARACTERISTICS (接下页)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURRENT CONTROL						
I_{REF}	xVREF input current	xVREF = 3.3 V	–3		3	µA
V_{TRIP}	xISENSE trip voltage	xVREF = 3.3 V, 100% current setting	635	660	685	mV
		xVREF = 3.3 V, 71% current setting	445	469	492	
		xVREF = 3.3 V, 38% current setting	225	251	276	
A_{ISENSE}	Current sense amplifier gain	Reference only		5		V/V

FUNCTIONAL DESCRIPTION

PWM Motor Drivers

The DRV8802 contains two H-bridge motor drivers with current-control PWM circuitry. A block diagram of the motor control circuitry is shown in 图 1.

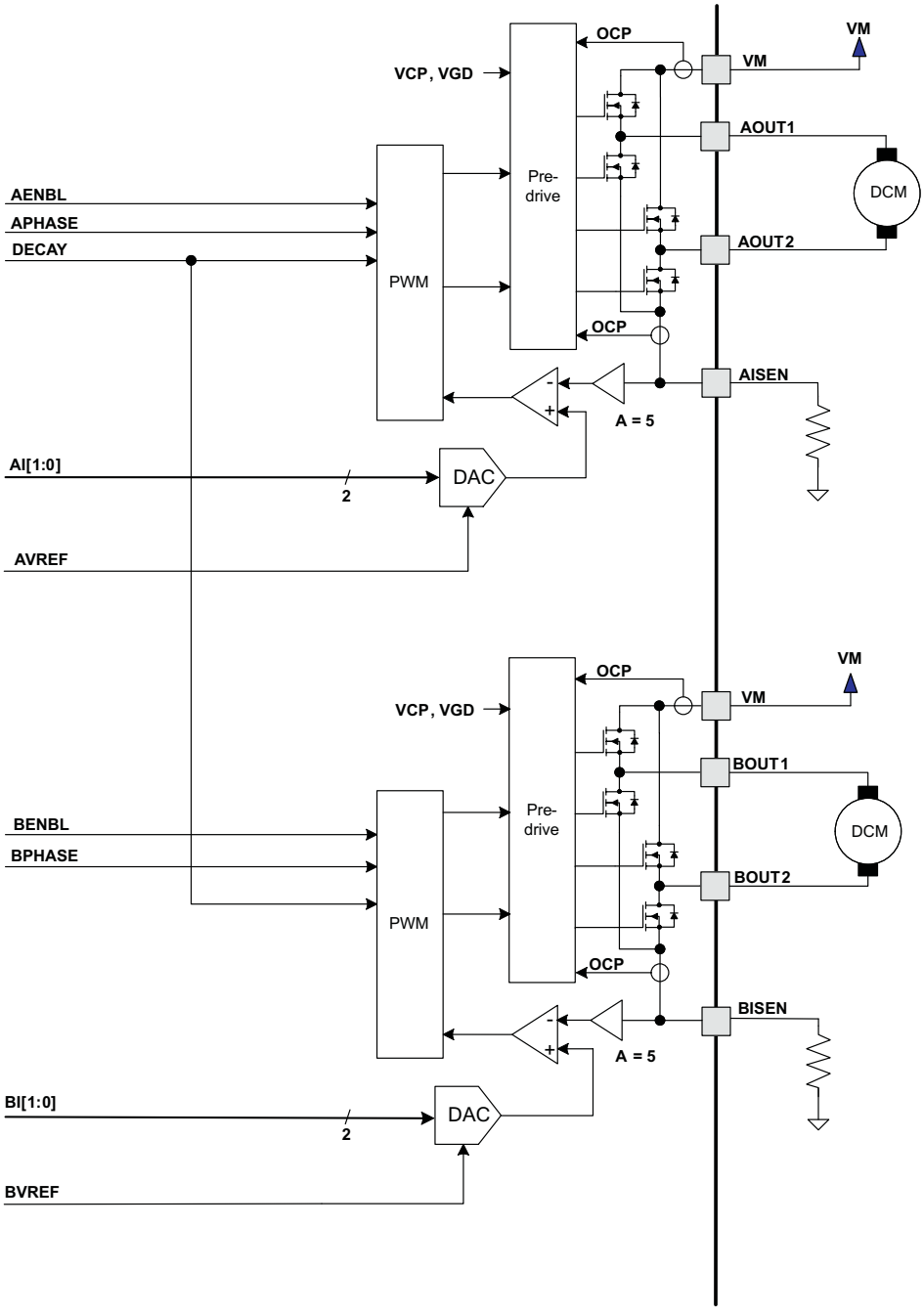


图 1. Motor Control Circuitry

Note that there are multiple VM pins. All VM pins must be connected together to the motor supply voltage.

Bridge Control

The xPHASE input pins control the direction of current flow through each H-bridge, and hence the direction of rotation of a DC motor. The xENBL input pins enable the H-bridge outputs when active high, and can also be used for PWM speed control of the motor. 表 2 shows the logic.

表 2. H-Bridge Logic

xENBL	xPHASE	xOUT1	xOUT2
0	X	see (1)	see (1)
1	1	H	L
1	0	L	H

(1) Depends on state of the DECAY pin. See Decay Mode and Braking section below.

Current Regulation

The current through the motor windings is regulated by a fixed-frequency PWM current regulation, or current chopping. When an H-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage and inductance of the winding. Once the current hits the current chopping threshold, the bridge disables the current until the beginning of the next PWM cycle.

For stepping motors, current regulation is normally used at all times, and can changing the current can be used to microstep the motor. For DC motors, current regulation is used to limit the start-up and stall current of the motor.

The PWM chopping current is set by a comparator which compares the voltage across a current sense resistor connected to the xISEN pins, multiplied by a factor of 5, with a reference voltage. The reference voltage is input from the xVREF pins, and is scaled by a 2-bit DAC that allows current settings of 100%, 71%, 38% of full-scale, plus zero.

The full-scale (100%) chopping current is calculated in 公式 1.

$$I_{CHOP} = \frac{V_{REFX}}{5 \bullet R_{ISENSE}} \quad (1)$$

Example:

If a 0.5-Ω sense resistor is used and the VREFx pin is 3.3 V, the full-scale (100%) chopping current will be 3.3 V / (5 x 0.5 Ω) = 1.32 A.

Two input pins per H-bridge (xI1 and xI0) are used to scale the current in each bridge as a percentage of the full-scale current set by the VREF input pin and sense resistance. The function of the pins is shown in 表 3.

表 3. H-Bridge Pin Functions

xI1	xI0	RELATIVE CURRENT (% FULL-SCALE CHOPPING CURRENT)
1	1	0% (Bridge disabled)
1	0	38%
0	1	71%
0	0	100%

Note that when both xI bits are 1, the H-bridge is disabled and no current flows.

Example:

If a 0.5-Ω sense resistor is used and the VREF pin is 3.3 V, the chopping current will be 1.32 A at the 100% setting (xI1, xI0 = 00). At the 71% setting (xI1, xI0 = 01) the current will be 1.32 A x 0.71 = 0.937 A, and at the 38% setting (xI1, xI0 = 10) the current will be 1.32 A x 0.38 = 0.502 A. If (xI1, xI0 = 11) the bridge will be disabled and no current will flow.

Decay Mode and Braking

During PWM current chopping, the H-bridge is enabled to drive current through the motor winding until the PWM current chopping threshold is reached. This is shown in 图 2 as case 1. The current flow direction shown indicates the state when the xENBL pin is high.

Once the chopping current threshold is reached, the H-bridge can operate in two different states, fast decay or slow decay.

In fast decay mode, once the PWM chopping current level has been reached, the H-bridge reverses state to allow winding current to flow in a reverse direction. As the winding current approaches zero, the bridge is disabled to prevent any reverse current flow. Fast decay mode is shown in 图 2 as case 2.

In slow decay mode, winding current is re-circulated by enabling both of the low-side FETs in the bridge. This is shown in 图 2 as case 3.

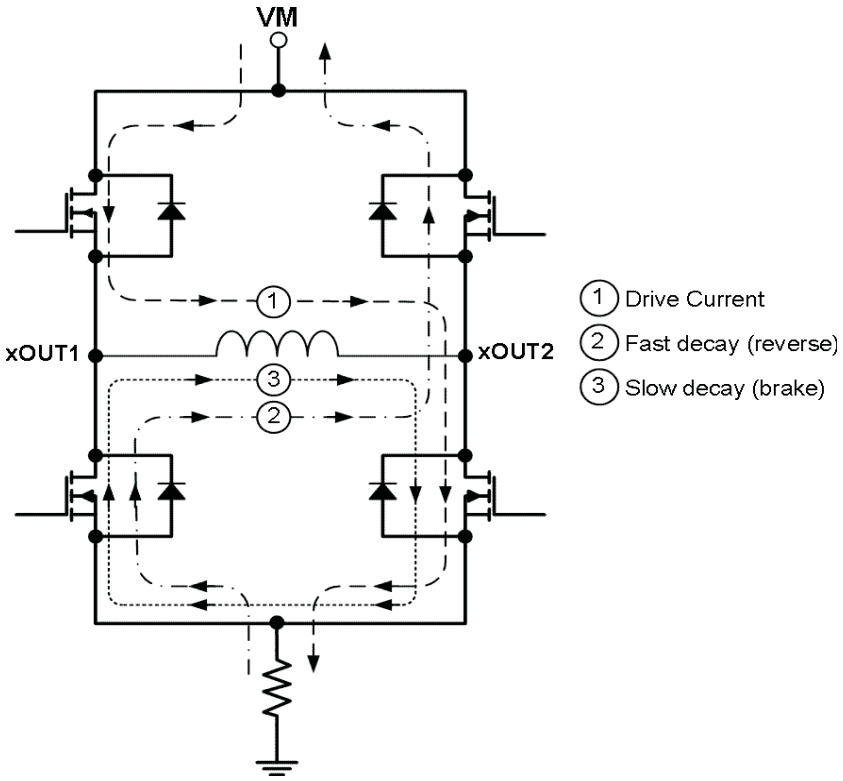


图 2. Decay Mode

The DRV8802 supports fast decay and slow decay mode. Slow or fast decay mode is selected by the state of the DECAY pin - logic low selects slow decay, and logic high sets fast decay mode. Note that the DECAY pin sets the decay mode for both H-bridges.

DECAY mode also affects the operation of the bridge when it is disabled (by taking the ENBL pin inactive). This applies if the ENABLE input is being used for PWM speed control of the motor, or if it is simply being used to start and stop motor rotation.

If the DECAY pin is high (fast decay), when the bridge is disabled, all FETs are turned off and decay current flows through the body diodes. This allows the motor to coast to a stop.

If the DECAY pin is low (slow decay), both low-side FETs will be turned on when ENBL is made inactive. This essentially shorts out the back EMF of the motor, causing the motor to brake, and stop quickly. The low-side FETs will stay in the ON state even after the current reaches zero.

Blanking Time

After the current is enabled in an H-bridge, the voltage on the xISEN pin is ignored for a fixed period of time before enabling the current sense circuitry. This blanking time is fixed at 3.75 µs. Note that the blanking time also sets the minimum on time of the PWM.

nRESET and nSLEEP Operation

The nRESET pin, when driven active low, resets the internal logic. It also disables the H-bridge drivers. All inputs are ignored while nRESET is active.

Driving nSLEEP low will put the device into a low power sleep state. In this state, the H-bridges are disabled, the gate drive charge pump is stopped, the V3P3OUT regulator is disabled, and all internal clocks are stopped. In this state all inputs are ignored until nSLEEP returns inactive high. When returning from sleep mode, some time (approximately 1 ms) needs to pass before the motor driver becomes fully operational.

Protection Circuits

The DRV8802 is fully protected against undervoltage, overcurrent and overtemperature events.

Overcurrent Protection (OCP)

An analog current limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than the OCP time, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. The device will remain disabled until either nRESET pin is applied, or VM is removed and re-applied.

Overcurrent conditions on both high and low side devices; i.e., a short to ground, supply, or across the motor winding will all result in an overcurrent shutdown. Note that overcurrent protection does not use the current sense circuitry used for PWM current control, and is independent of the I_{SENSE} resistor value or VREF voltage.

Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. Once the die temperature has fallen to a safe level operation will automatically resume.

Undervoltage Lockout (UVLO)

If at any time the voltage on the VM pins falls below the undervoltage lockout threshold voltage, all circuitry in the device will be disabled and internal logic will be reset. Operation will resume when V_M rises above the UVLO threshold.

THERMAL INFORMATION

Thermal Protection

The DRV8802 has thermal shutdown (TSD) as described above. If the die temperature exceeds approximately 150°C, the device will be disabled until the temperature drops to a safe level.

Any tendency of the device to enter TSD is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

Power Dissipation

Power dissipation in the DRV8802 is dominated by the power dissipated in the output FET resistance, or RDS(ON). Average power dissipation of each H-bridge when running a DC motor can be roughly estimated by 公式 2.

$$P = 2 \bullet R_{DS(ON)} \bullet (I_{OUT})^2 \quad (2)$$

where P is the power dissipation of one H-bridge, $R_{DS(ON)}$ is the resistance of each FET, and I_{OUT} is the RMS output current being applied to each winding. I_{OUT} is equal to the average current drawn by the DC motor. Note that at start-up and fault conditions this current is much higher than normal running current; these peak currents and their duration also need to be taken into consideration. The factor of 2 comes from the fact that at any instant two FETs are conducting winding current (one high-side and one low-side).

The total device dissipation will be the power dissipated in each of the two H-bridges added together.

The maximum amount of power that can be dissipated in the device is dependent on ambient temperature and heatsinking.

Note that $R_{DS(ON)}$ increases with temperature, so as the device heats, the power dissipation increases. This must be taken into consideration when sizing the heatsink.

Heatsinking

The PowerPAD™ package uses an exposed pad to remove heat from the device. For proper operation, this pad must be thermally connected to copper on the PCB to dissipate heat. On a multi-layer PCB with a ground plane, this can be accomplished by adding a number of vias to connect the thermal pad to the ground plane. On PCBs without internal planes, copper area can be added on either side of the PCB to dissipate heat. If the copper area is on the opposite side of the PCB from the device, thermal vias are used to transfer the heat between top and bottom layers.

For details about how to design the PCB, refer to TI application report SLMA002, " PowerPAD™ Thermally Enhanced Package" and TI application brief SLMA004, " PowerPAD™ Made Easy", available at www.ti.com.

In general, the more copper area that can be provided, the more power can be dissipated.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/ Ball Finish	MSL Peak Temp (3)	Samples (Requires Login)
DRV8802PWP	ACTIVE	HTSSOP	PWP	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
DRV8802PWPR	ACTIVE	HTSSOP	PWP	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	

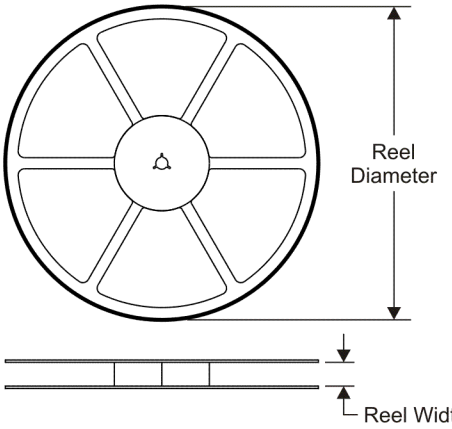
(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

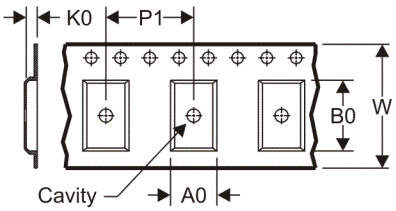
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

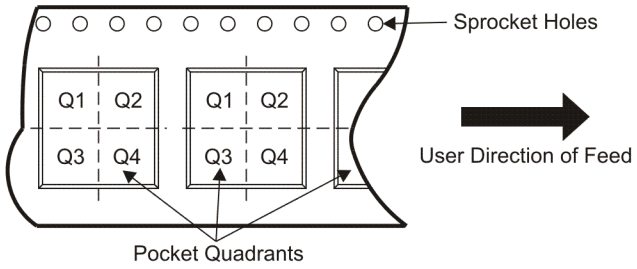


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

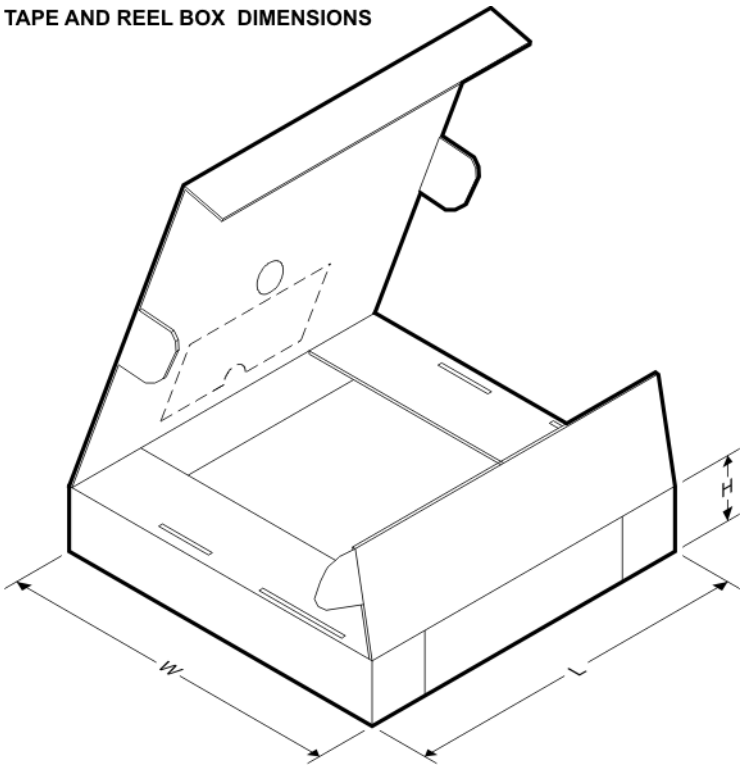
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8802PWPR	HTSSOP	PWP	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

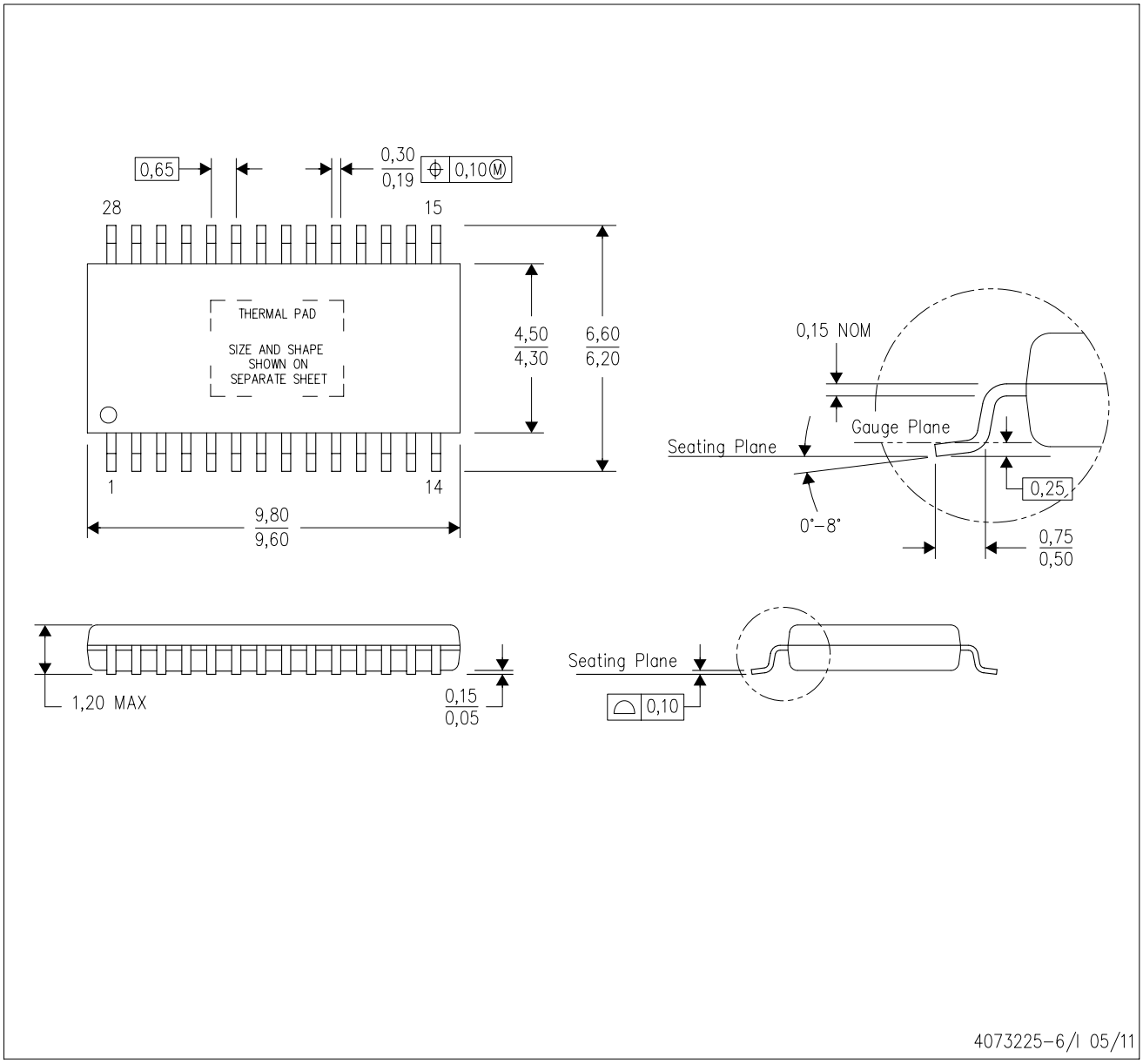
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8802PWPR	HTSSOP	PWP	28	2000	346.0	346.0	33.0

PWP (R–PDSO–G28) PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <http://www.ti.com>.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
E. Falls within JEDEC MO–153

PowerPAD is a trademark of Texas Instruments.

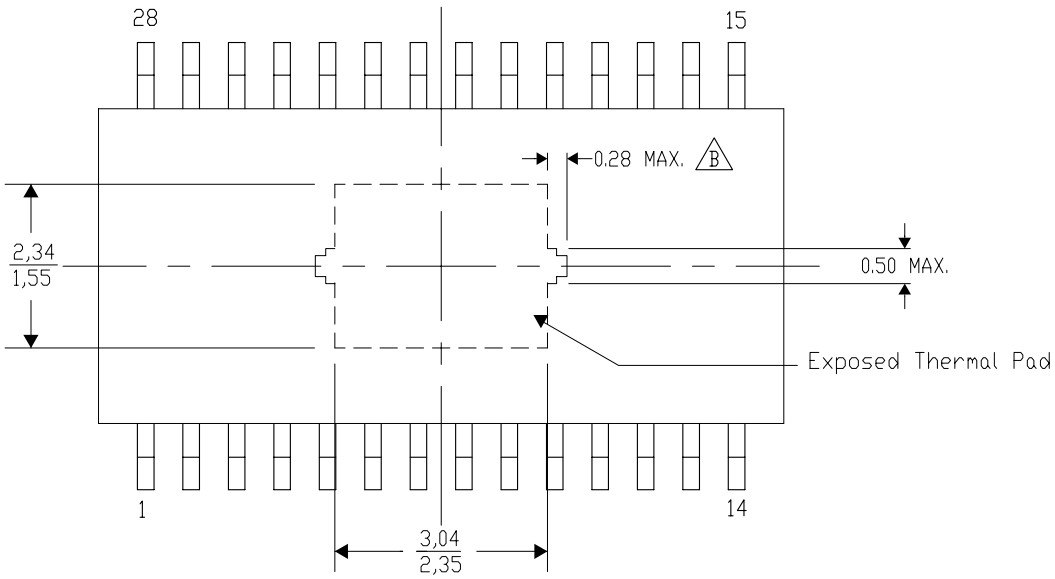
PWP (R–PDSO–G28) PowerPAD™ SMALL PLASTIC OUTLINE

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Top View

Exposed Thermal Pad Dimensions

4206332–29/W 05/11

NOTE: A. All linear dimensions are in millimeters

B. Exposed tie strap features may not be present.

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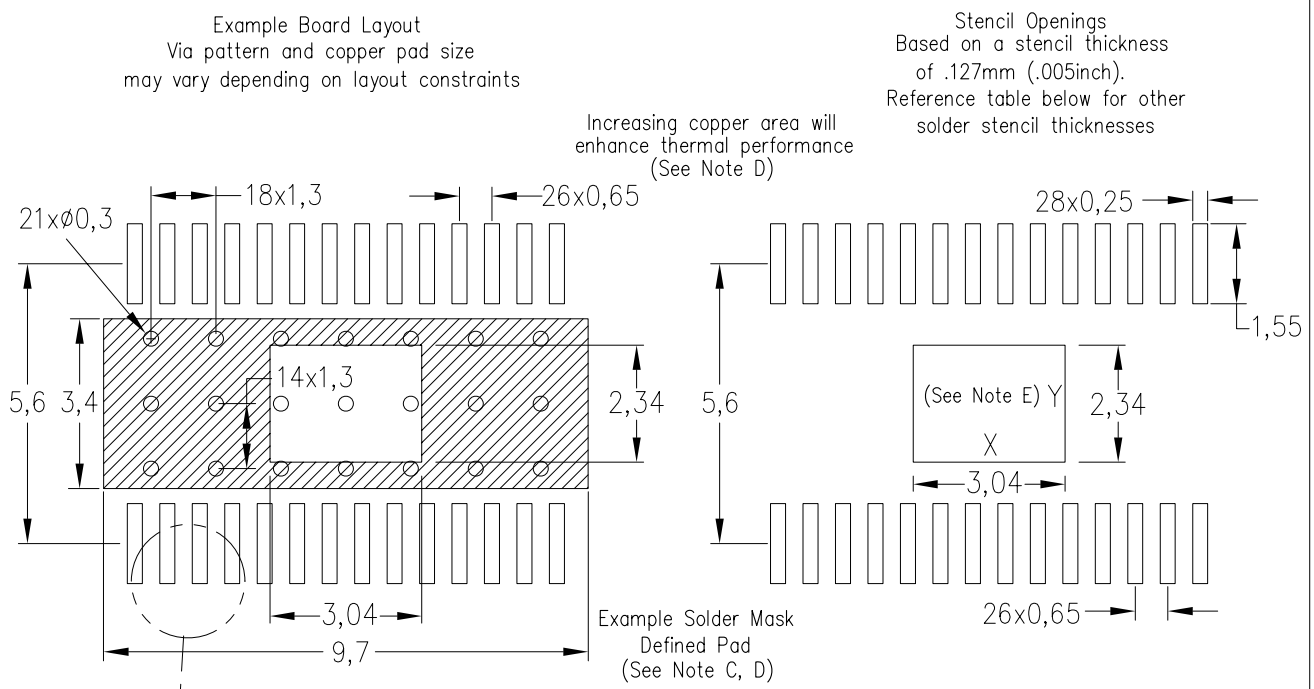
PWP (R–PDSO–G28) PowerPAD™ PLASTIC SMALL OUTLINE



Center Power Pad Solder Stencil Opening		
Stencil Thickness	X	Y
0.1mm	3.26	2.50
0.127mm	3.04	2.34
0.152mm	2.85	2.18
0.178mm	2.64	2.09

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.
F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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